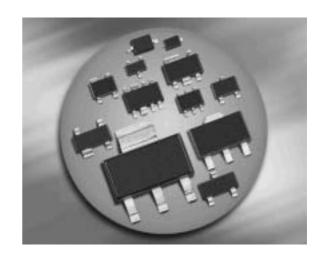


## **Silicon Tuning Diodes**

- Extended frequency range up to 2.5 GHz;
   spezial design for use in TV-sat tuners
- High capacitance ratio
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101







#### **BB833**



Туре	Package	Configuration	<b>L</b> S(nH)	Marking
BB833	SOD323	single	1.8	white X

**Maximum Ratings** at  $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_{R}$	30	V
Peak reverse voltage-	$V_{RM}$	35	
$R \ge 5 k\Omega$			
Forward current	I <sub>F</sub>	20	mA
Operating temperature range	$T_{op}$	-55 150	°C
Storage temperature	$T_{ m stg}$	-55 150	

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<sup>&</sup>lt;sup>1</sup>Pb-containing package may be available upon special request



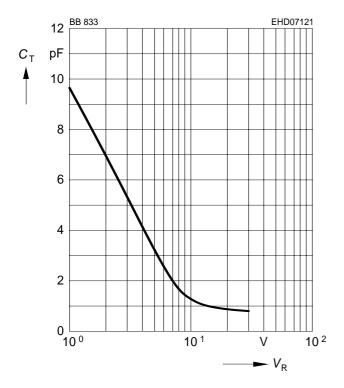
# **Electrical Characteristics** at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	1
DC Characteristics	•		•		
Reverse current	$I_{R}$	-	-		nA
<i>V</i> <sub>R</sub> = 30 V		_	-	20	
$V_{R} = 30 \text{ V}, T_{A} = 85 ^{\circ}\text{C}$				500	
AC Characteristics					
Diode capacitance	$C_{T}$				pF
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$		8.5	9.3	10	
$V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$		0.6	0.75	0.9	
Capacitance ratio	C <sub>T1</sub> /C <sub>T28</sub>	11	12.4	-	
$V_{R} = 1 \text{ V}, V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching <sup>1)</sup>	$\Delta C_{T}/C_{T}$	-	-	3	%
$V_{R} = 1 \text{ V}, V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$					
Series resistance	r <sub>S</sub>	-	1.8	-	Ω
$V_{R} = 1 \text{ V}, f = 470 \text{ MHz}$					

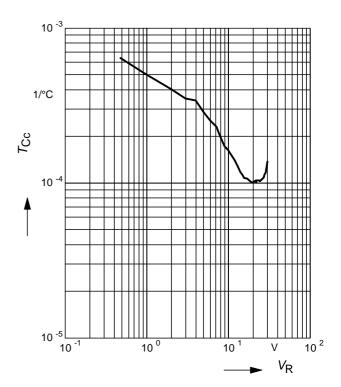
<sup>&</sup>lt;sup>1</sup>For details please refer to Application Note 047.



# **Diode capacitance** $C_T = f(V_R)$ f = 1MHz



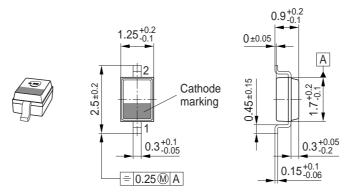
# Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



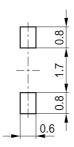
3 2007-04-20



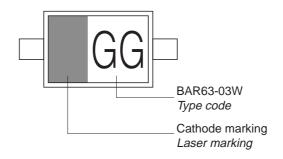
# Package Outline



#### Foot Print

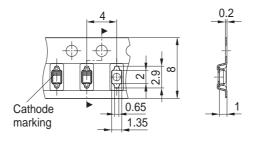


## Marking Layout (Example)



# Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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